

**Amendments to the Specification**

Please replace the paragraph beginning on page 12, line 9, with the following rewritten paragraph:

In the manufacturing method, as shown in FIG. 3A and FIG. 3B, an insulating layer 2 made of an insulating material such as alumina ( $Al_2O_3$ ) or silicon dioxide ( $SiO_2$ ) whose thickness is 1 to 20  $\mu m$ , for example, is formed through sputtering, for example, on a substrate 1 made of a ceramic material such as aluminum oxide and titanium carbide ( $Al_2O_3-TiC$ ). On the insulating layer 2 a bottom shield layer 3 made of a magnetic material and having a thickness of 0.1 to 5  $\mu m$ , for example, is formed for making a read head. The bottom shield layer 3 is made of a magnetic material such as ~~FeAiSiFeAlSi~~, NiFe, CoFe, CoFeNi, FeN, FeZrN, FeTaN, CoZrNb, or CoZrTa. The bottom shield layer 3 is formed through sputtering or plating.